

60V 11.5mohm N-channel SGT MOSFET
AKG6N115GL

Description:

This N channel SGT MOSFET has been designed to low on-state resistance and low switching loss, especial for DC-DC application.

Features:

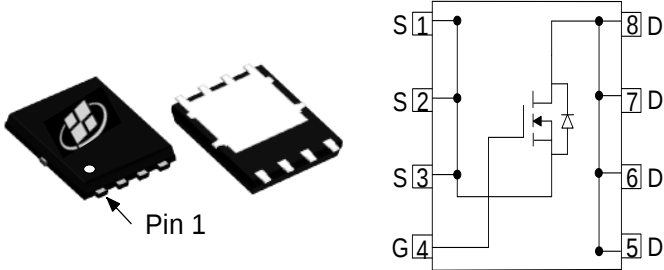
- Low $R_{DS(ON)}$
- RoHS compliant ^(Note 1)
- Halogen-free ^(Note 1)
- 100% UIS tested

Applications:

- Battery Management System
- Motor Drivers
- DC-DC Converter

Key Performance Parameters:

Parameter	Value	Unit
V_{DS}	60	V
$R_{DS(ON), max} @V_{GS} = 10V$	11.5	mΩ
I_D	49	A



Ordering Information:

Ordering Code	Package Type	Marking Code	Form	Packing
AKG6N115GL	PDFN5X6	G6N115GL	Tape Reel	5000PCS

Notes:

1. Contact ALKAIDSEMI sales for detail information

Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{DS}	Drain-Source Voltage	60	V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$) ^(Note 1)	49	A
	Drain Current - Continuous ($T_C = 100^\circ\text{C}$)	31	A
I_{DM}	Drain Current - Pulsed ^(Note 3)	196	A
V_{GS}	Gate-Source Voltage	± 20	V
E_{AS}	Single Pulsed Avalanche Energy ^(Note 4)	42	mJ
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$)	44	W
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Value	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Steady-State	2.8	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Steady State ^(Note 5)	45	$^\circ\text{C}/\text{W}$

Notes:

1. The max drain current rating is silicon limited
2. The max drain current rating is package limited
3. Repetitive Rating: Pulse width limited by maximum junction temperature
4. $L = 0.5 \text{ mH}$, $V_{DD} = 30 \text{ V}$, $I_{AS} = 13 \text{ A}$, $R_G = 25 \Omega$, Starting $T_J = 25^\circ\text{C}$
5. Mount on minimum PCB layout

Electrical Characteristics (T _J = 25°C unless otherwise noted)						
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	60			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 60 V, V _{GS} = 0 V			1	μA
I _{GSS}	Gate Leakage Current	V _{GS} = ± 20 V, V _{DS} = 0 V			± 100	nA
V _{GS(TH)}	Gate Threshold voltage	V _{DS} = V _{GS} , I _D = 250 μA	1	1.6	2.5	V
R _{DS(ON)}	Drain-Source on-state resistance	V _{GS} = 10 V, I _D = 30 A		9.5	11.5	mΩ
		V _{GS} = 4.5 V, I _D = 30 A		13.5	18	mΩ
Dynamic Characteristics						
C _{ISS}	Input Capacitance	V _{DS} = 30 V, V _{GS} = 0 V, F = 1 MHz		1190		pF
C _{OSS}	Output Capacitance			250		pF
C _{RSS}	Reverse Transfer Capacitance			30		pF
R _G	Gate Resistance	F = 1 MHz		1.3		Ω
Switching Characteristics						
T _{D(ON)}	Turn On Delay Time	V _{DD} = 30 V , R _L = 1.5 Ω, V _{GS} = 10 V, R _G = 6 Ω		8		nS
T _R	Rise Time			30		nS
T _{D(OFF)}	Turn Off Delay Time			23		nS
T _F	Fall Time			10		nS
Q _G	Total Gate Charge	V _{DD} = 30 V , I _D = 20 A, V _{GS} = 10 V		22.5		nC
Q _{GS}	Gate-Source Charge			4.5		nC
Q _{GD}	Gate-Drain Charge			6.5		nC
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Body-Diode Forward Current				49	A
I _{SM}	Maximum Pulsed Body-Diode Forward Current ^(NOTE 1)				196	A
V _{SD}	Diode Forward Voltage	V _{GS} = 0 V, I _S = 20 A		0.92		V
T _{RR}	Reverse recovery time	V _{DD} = 30 V, I _D = 15 A, di/dt = 100 A/μS		27		nS
Q _{RR}	Reverse recovery charge			20		nC
I _{RRM}	Peak Reverse Recovery Current			1.3		A

Electrical Characteristics Diagrams

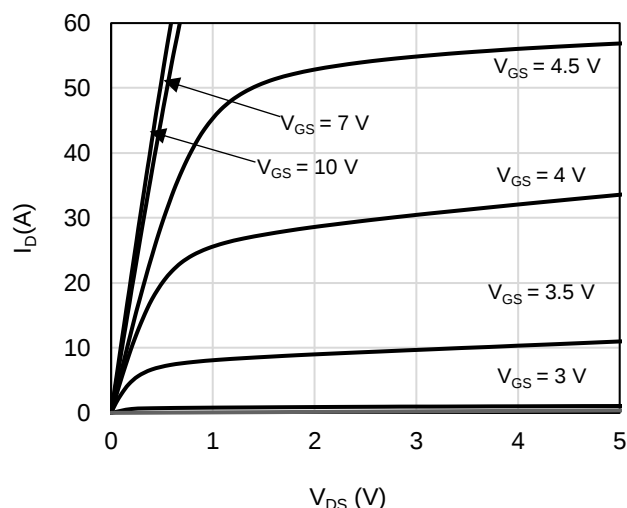


Figure 1: On-Region Characteristics

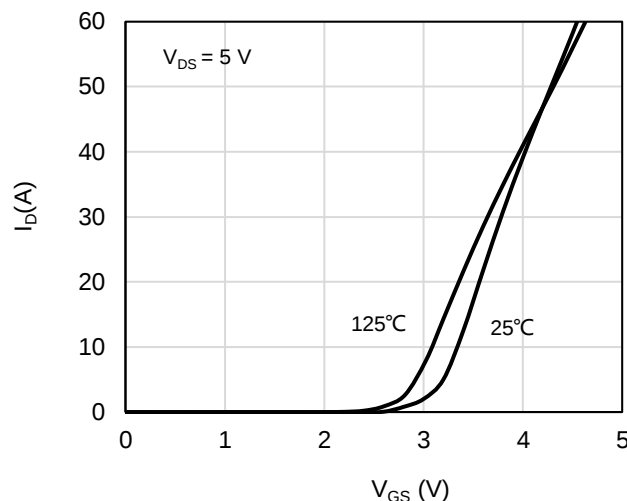


Figure 2: Transfer Characteristics

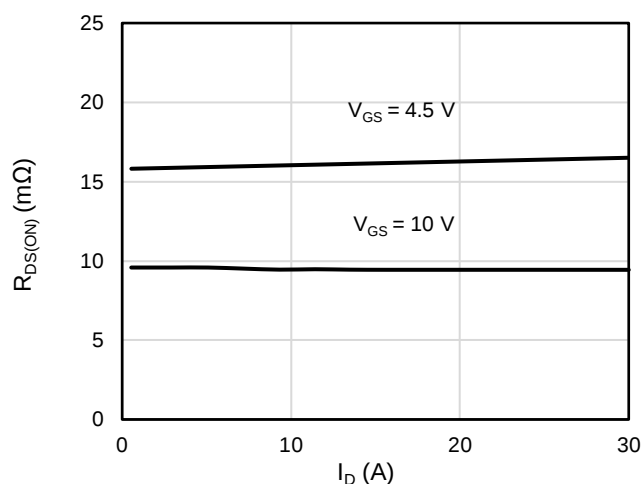


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

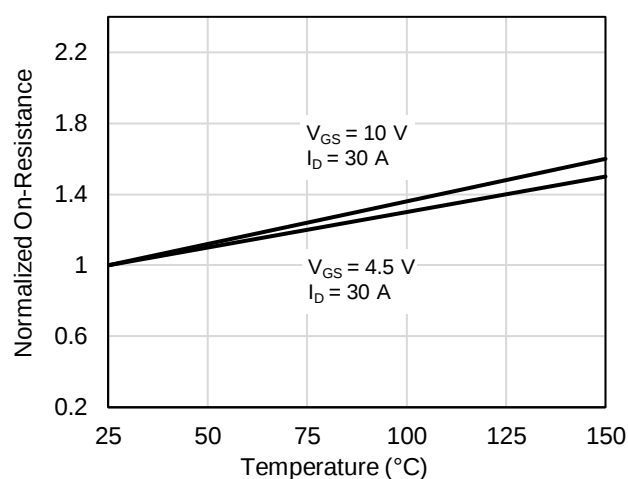


Figure 4: On-Resistance vs. Junction Temperature

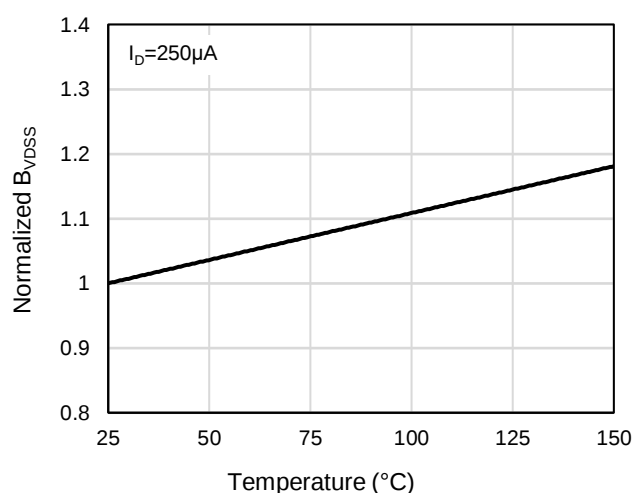


Figure 5: Breakdown Voltage vs. Junction Temperature

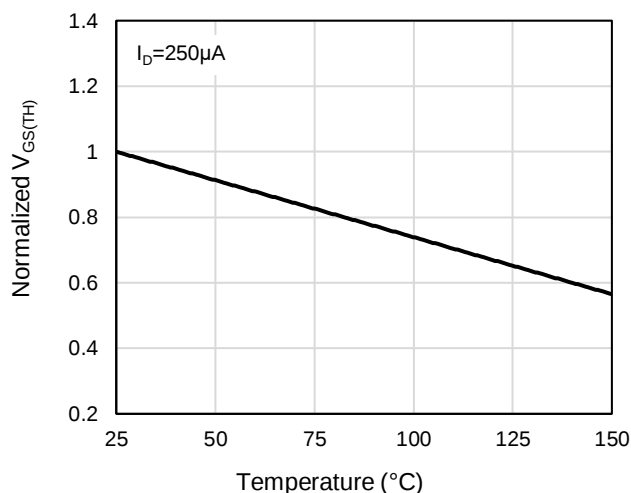


Figure 6: Threshold Voltage vs. Junction Temperature

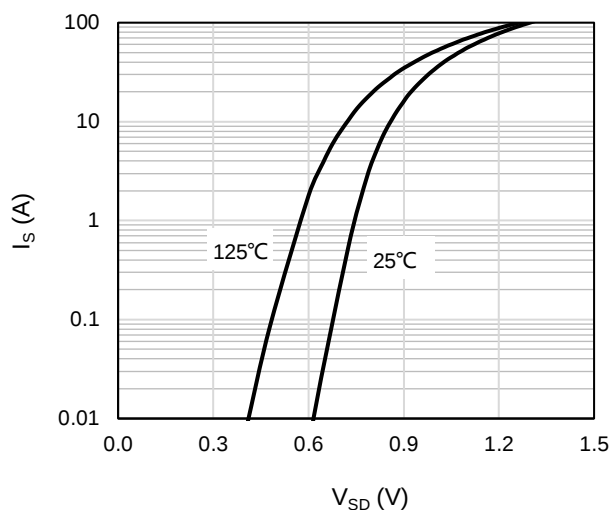


Figure 7: Body-Diode Characteristics

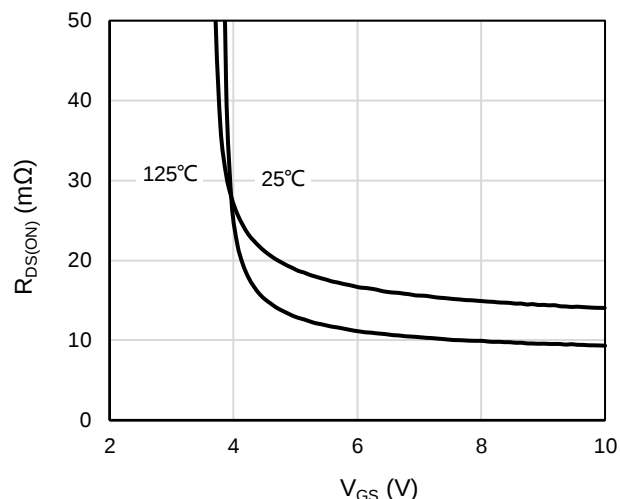


Figure 8: On-Resistance vs. Gate-Source Voltage

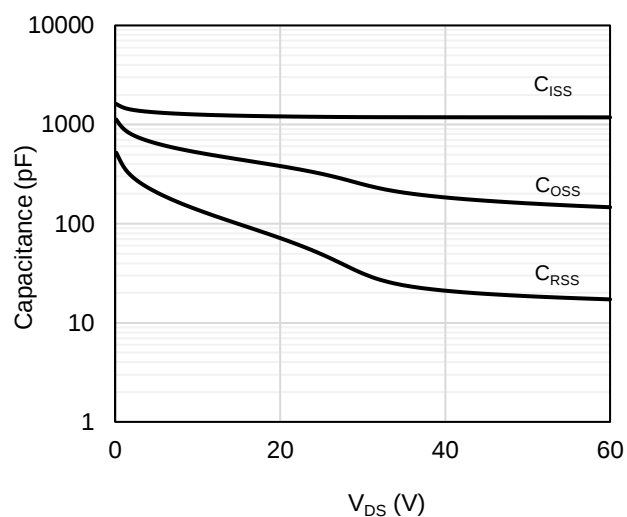


Figure 9: Capacitance Characteristics

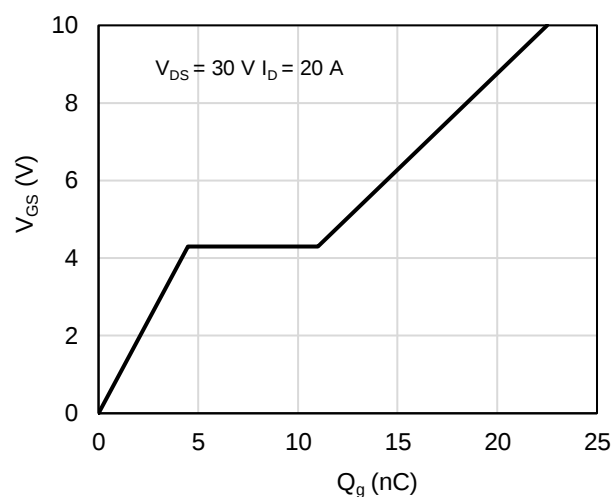


Figure 10: Gate-Charge Characteristics

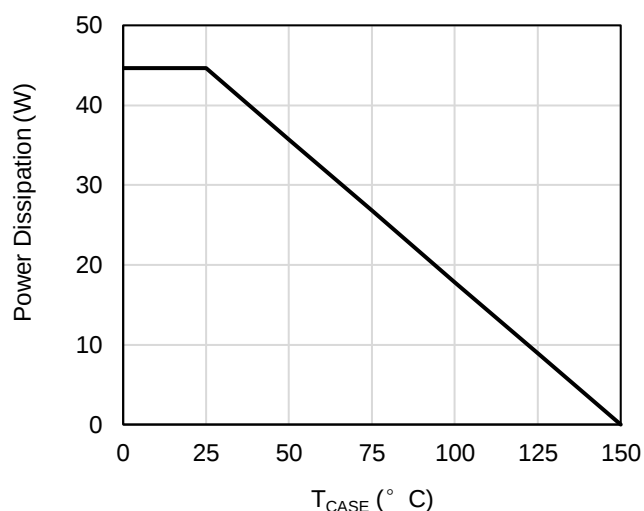


Figure 11: Power De-rating

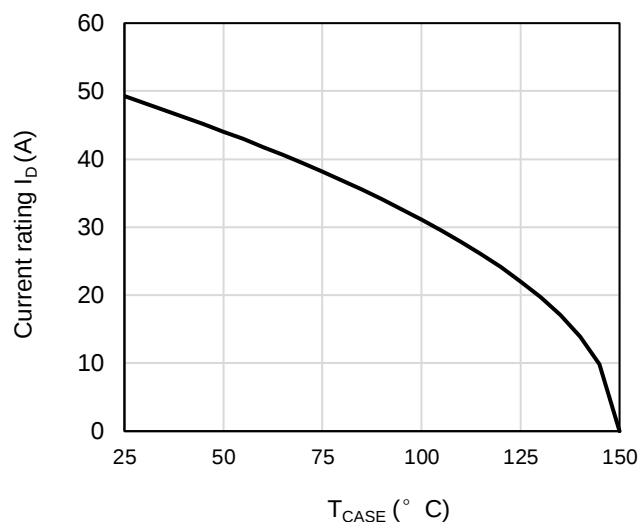
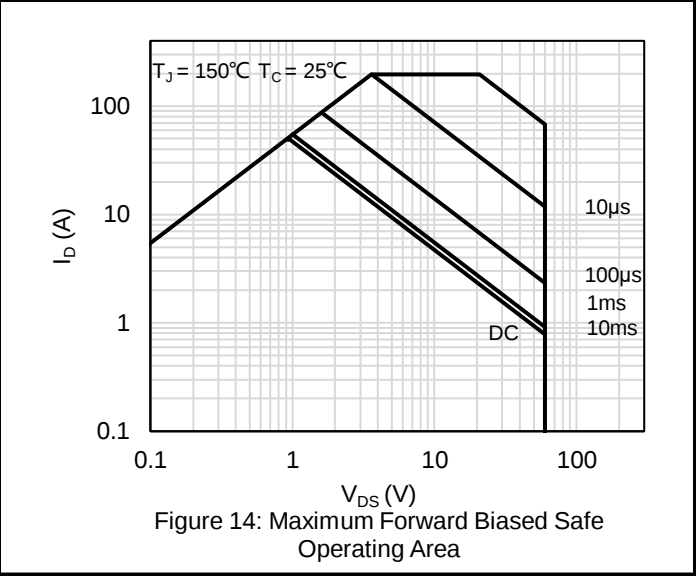
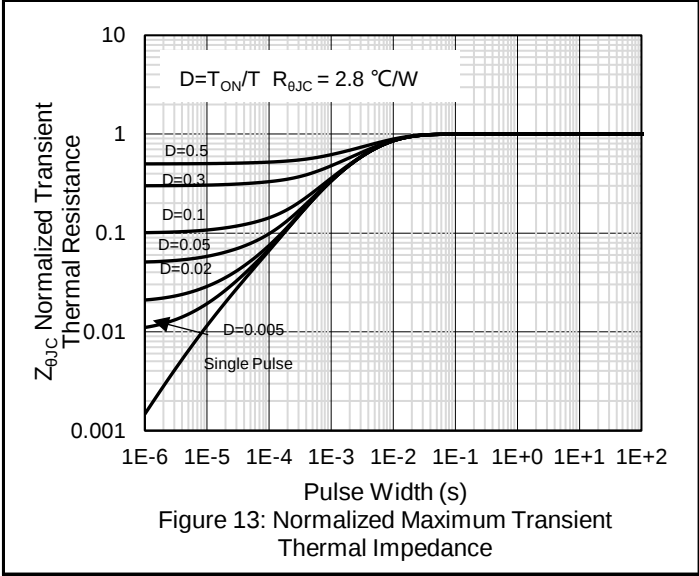
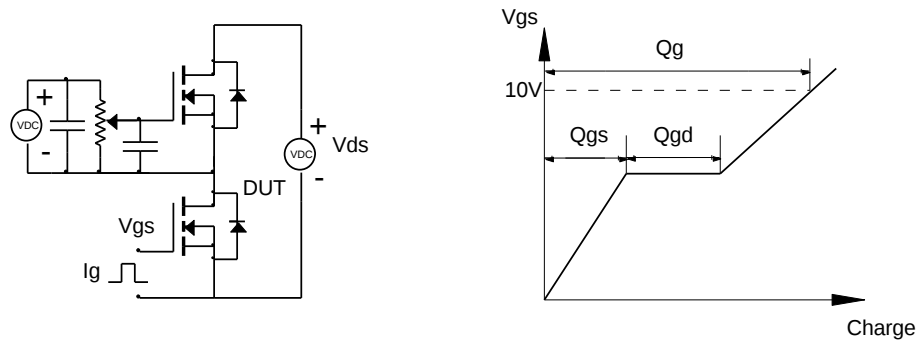


Figure 12: Current De-rating

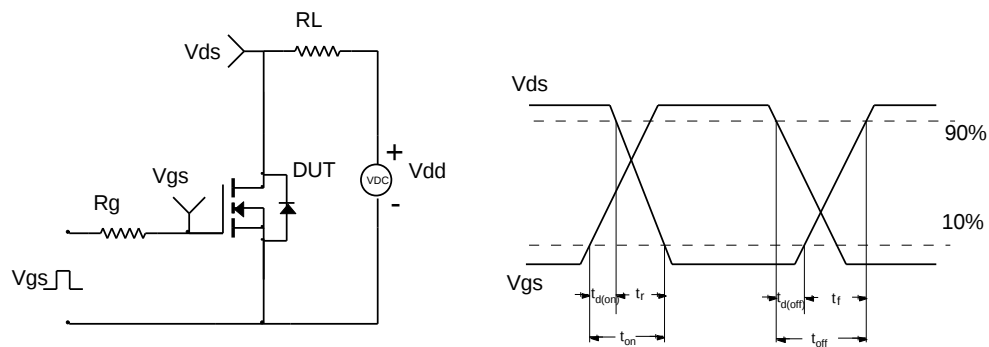


Test Circuit and Waveform

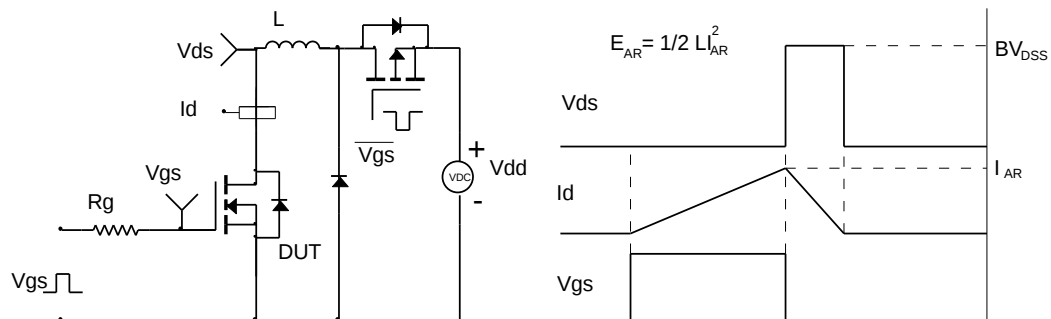
Gate Charge Test Circuit & Waveform



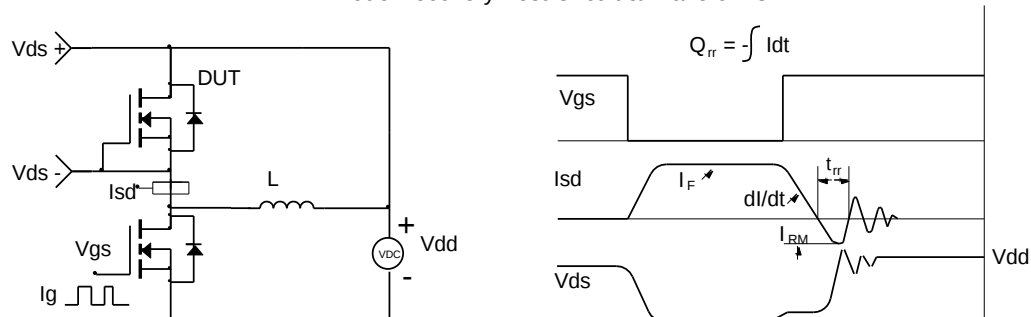
Resistive Switching Test Circuit & Waveforms



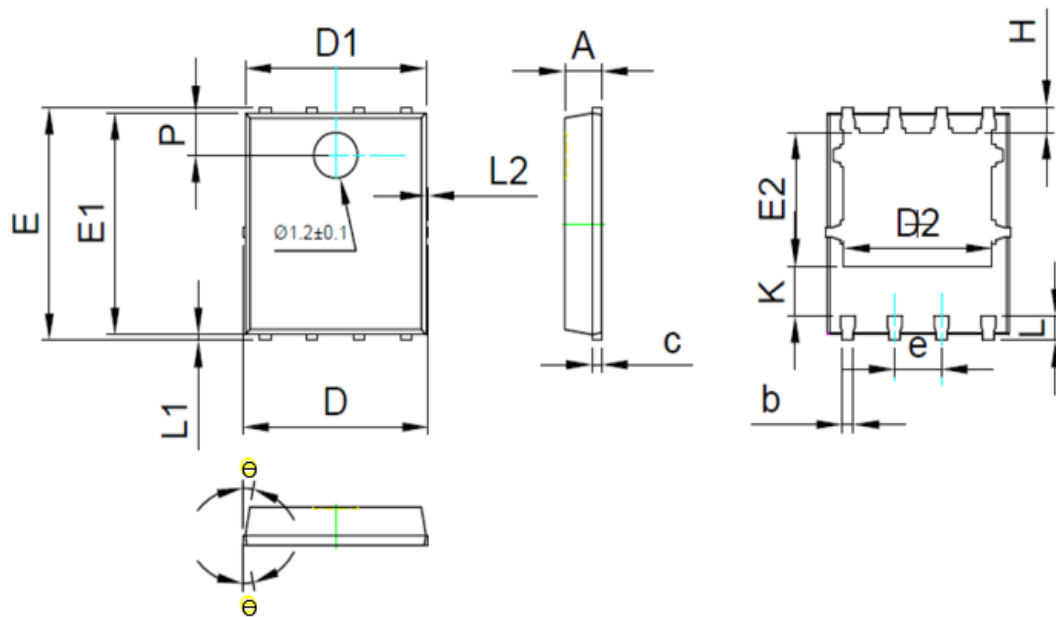
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Package Outlines



COMMON DIMENSIONS
(UNITS OF MEASURE = MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	0.90	1.00	1.10
b	0.35	0.40	0.45
c	0.21	0.25	0.34
D	-	-	5.1
D1	4.85	4.90	4.95
D2	3.96	4.01	4.06
e	1.27 BSC		
E	5.95	6.00	6.05
E1	5.70	5.75	5.80
E2	3.425	3.475	3.525
H	0.60	0.65	0.70
K	1.29	-	-
L	0.60	0.65	0.70
L1	0.05	0.15	0.25
L2	-	-	0.12
Θ	8°	10°	12°
P	1.05	1.10	1.15

Marking Information

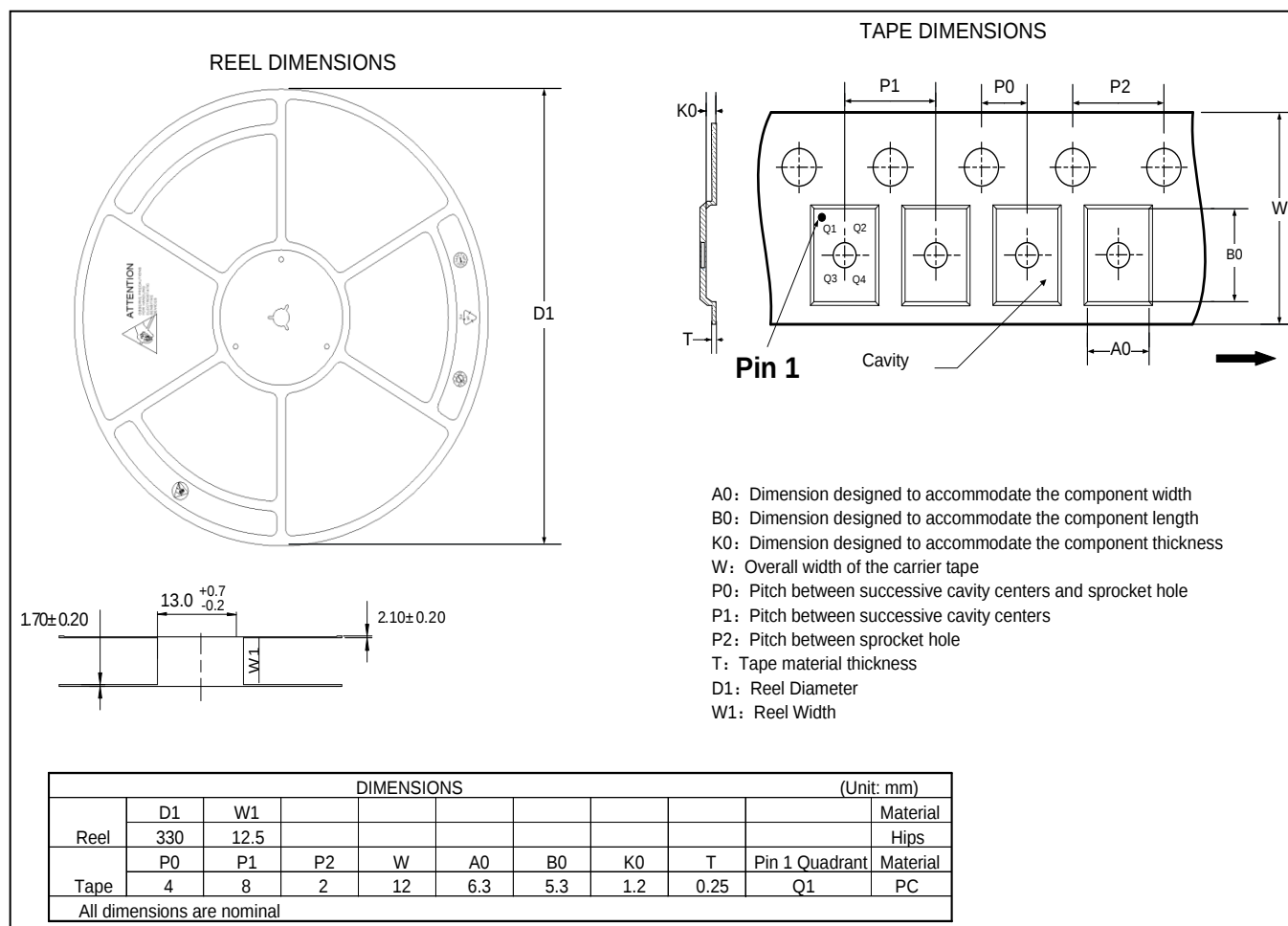


Note:

G6N115GL = Product Name Code

XXXXXXX = Date code

Contact ALKAIDSEMI sales for detail information



Revision History

Revision	Release Date	Remark
Rev.1.0	2022/7/13	Initial Release

Disclaimer

The information given in this document describes the independent performance of the product, but similar performance is not guaranteed under other working conditions, and cannot be guaranteed when installed with other products or equipment. To achieve the required performance of the product in actual scenarios, the customer should conduct a complete application test to assess the functionality of the product.

Alkaidsemi assumes no responsibility for equipment failures result from using products at values that exceed the ratings, operating conditions, or other parameters listed in the product specifications.

The product described in this specification is not applicable for aerospace or other applications which requires high reliability. Customers using or selling these products for use in medical, life-saving, or life-sustaining applications do so at their own risk and agree to fully indemnify.

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